Mingxing Wang

List of Publications by Year
in descending order

293 papers	7,202 citations	76294 40 h-index	82499 72 g-index
295 all docs	295 docs citations	295 times ranked	7883 citing authors

#	Article	IF	Citations
1	X-ray photoelectron spectroscopy and auger electron spectroscopy studies of Al-doped ZnO films. Applied Surface Science, 2000, 158, 134-140.	3.1	1,227
2	Generation and electric control of spinâ€“valley-coupled circular photogalvanic current in WSe2. Nature Nanotechnology, 2014, 9, 851-857.	15.6	278
3	Robustness of topological order and formation of quantum well states in topological insulators exposed to ambient environment. Proceedings of the National Academy of Sciences of the United States of America, 2012, 109, 3694-3698.	3.3	158
4	Molecular beam epitaxy growth of GaN, AlN and InN. Progress in Crystal Growth and Characterization of Materials, 2004, 48-49, 42-103.	1.8	153
5	Nitrogen doped ZnO film grown by the plasma-assisted metal-organic chemical vapor deposition. Journal of Crystal Growth, 2001, 226, 123-129.	0.7	123
6	Polarity and Its Influence on Growth Mechanism during MOVPE Growth of GaN Sub-micrometer Rods. Crystal Growth and Design, 2011, 11, 1573-1577.	1.4	113
7	Proposal and achievement of novel structure InNâˆ•GaN multiple quantum wells consisting of 1 ML and fractional monolayer InN wells inserted in GaN matrix. Applied Physics Letters, 2007, 90, 073101.	1.5	111
8	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. Scientific Reports, 2016, 6, 35934.	1.6	110
9	X-ray photoelectron spectroscopy study of ZnO films grown by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2003, 252, 180-183.	0.7	101
10	Physical origin of Davydov splitting and resonant Raman spectroscopy of Davydov components in multilayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">MoTe</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2016, 93, .	1.1	93
11	Crystal growth of undoped ZnO films on Si substrates under different sputtering conditions. Journal of Crystal Growth, 2002, 243, 439-443.	0.7	85
12	High-Electron-Mobility InN Layers Grown by Boundary-Temperature-Controlled Epitaxy. Applied Physics Express, 2012, 5, 015502.	1.1	84
13	Effect of post-thermal annealing on properties of ZnO thin film grown on c-Al2O3 by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2003, 252, 275-278.	0.7	75
14	Phonon lifetimes and phonon decay in InN. Applied Physics Letters, 2005, 86, 223501.	1.5	75
15	Highâ€Outputâ€Power Ultraviolet Light Source from Quasiâ€2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	11.1	72
16	Effect of epitaxial temperature on N-polar InN films grown by molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 073512.	1.1	69
17	Polarity control of ZnO films grown on nitrided c-sapphire by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011921.	1.5	68
18	Step-Flow Growth of In-Polar InN by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2006, 45, L730-L733.	0.8	67

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19	Systematic study on p-type doping control of InN with different Mg concentrations in both In and N polarities. Applied Physics Letters, 2007, 91, 242111.	1.5	67
20	Secâ€Eliminating the SARSâ€CoVâ€2 by AlGaN Based High Power Deep Ultraviolet Light Source. Advanced Functional Materials, 2021, 31, 2008452.	7.8	67
21	Threading dislocations in In-polar InN films and their effects on surface morphology and electrical properties. Applied Physics Letters, 2007, 90, 151901.	1.5	66
22	Efficient silicon quantum dots light emitting diodes with an inverted device structure. Journal of Materials Chemistry C, 2016, 4, 673-677.	2.7	64
23	Growth and properties of Mg-doped In-polar InN films. Applied Physics Letters, 2007, 90, 201913.	1.5	62
24	Hole mobility in Mg-doped p-type InN films. Applied Physics Letters, 2008, 92, .	1.5	58
25	High mobility AlGaN/GaN heterostructures grown on Si substrates using a large lattice-mismatch induced stress control technology. Applied Physics Letters, 2015, 106, .	1.5	55
26	Experimental determination of strain-free Raman frequencies and deformation potentials for the E2 high and A1(LO) modes in hexagonal InN. Applied Physics Letters, 2006, 89, 171907.	1.5	53
27	Epitaxial growth of AlN films on sapphire via a multilayer structure adopting a low- and high-temperature alternation technique. CrystEngComm, 2015, 17, 7496-7499.	1.3	53
28	Growth of high quality and uniformity AlGaN/GaN heterostructures on Si substrates using a single AlGaN layer with low Al composition. Scientific Reports, 2016, 6, 23020.	1.6	52
29	Identification of Helicity-Dependent Photocurrents from Topological Surface States in Bi2Se3 Gated by Ionic Liquid. Scientific Reports, 2014, 4, 4889.	1.6	51
30	Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene. Advanced Functional Materials, 2019, 29, 1905056.	7.8	51
31	High-temperature annealing induced evolution of strain in AlN epitaxial films grown on sapphire substrates. Applied Physics Letters, 2019, 114, .	1.5	51
32	Fabrication and characterization of novel monolayer InN quantum wells in a GaN matrix. Journal of Vacuum Science & Technology B, 2008, 26, 1551.	1.3	50
33	Recent advances and challenges for successful pâ€type control of InN films with Mg acceptor doping by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1011-1023.	0.8	48
34	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. Applied Physics Letters, 2014, 104, .	1.5	48
35	High conductive gate leakage current channels induced by In segregation around screw- and mixed-type threading dislocations in lattice-matched InxAl1â^'xN/GaN heterostructures. Applied Physics Letters, 2010, 97, .	1.5	47
36	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. Physical Review Letters, 2018, 121, 145505.	2.9	45

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37	Influence of strain on the band gap energy of wurtzite InN. Physica Status Solidi (B): Basic Research, 2009, 246, 1177-1180.	0.7	44
38	Rashba and Dresselhaus spin-orbit coupling in GaN-based heterostructures probed by the circular photogalvanic effect under uniaxial strain. Applied Physics Letters, 2010, 97, .	1.5	43
39	k-space imaging of anisotropic 2D electron gas in GaN/GaAlN high-electron-mobility transistor heterostructures. Nature Communications, 2018, 9, 2653.	5.8	43
40	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	3.6	43
41	InN Thin Film Lattice Dynamics by Grazing Incidence Inelastic X-Ray Scattering. Physical Review Letters, 2011, 106, 205501.	2.9	41
42	Tunable Surface Electron Spin Splitting with Electric Double-Layer Transistors Based on InN. Nano Letters, 2013, 13, 2024-2029.	4.5	41
43	Grapheneâ€Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Nonâ€Polar Sapphire Substrates for Green Light Emitting Diodes. Advanced Functional Materials, 2020, 30, 2001283.	7.8	41
44	Molecular Beam Epitaxy Growth of Single-Domain and High-Quality ZnO Layers on Nitrided (0001) Sapphire Surface. Japanese Journal of Applied Physics, 2003, 42, L99-L101.	0.8	39
45	Preparation of H2 and LPG gas sensor. Sensors and Actuators B: Chemical, 2002, 84, 95-97.	4.0	38
46	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGaN quantum wells. Physical Review Materials, 2018, 2, .	0.9	36
47	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. Nano Letters, 2016, 16, 1328-1334.	4.5	35
48	Polarity inversion in high Mg-doped In-polar InN epitaxial layers. Applied Physics Letters, 2007, 91, .	1.5	34
49	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. Scientific Reports, 2017, 7, 42747.	1.6	33
50	Deepâ€Ultraviolet Microâ€LEDs Exhibiting High Output Power and High Modulation Bandwidth Simultaneously. Advanced Materials, 2022, 34, e2109765.	11.1	33
51	ZnO thin film grown on silicon by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2002, 243, 13-18.	0.7	32
52	Advances in InN epitaxy and its material control by MBE towards novel InN-based QWs. Journal of Crystal Growth, 2009, 311, 2073-2079.	0.7	32
53	Temperature-controlled epitaxy of InxGa1-xN alloys and their band gap bowing. Journal of Applied Physics, 2011, 110, 113514.	1.1	32
54	Residual stress in AlN films grown on sapphire substrates by molecular beam epitaxy. Superlattices and Microstructures, 2016, 93, 27-31.	1.4	32

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55	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. Advanced Electronic Materials, 2019, 5, 1800651.	2.6	32
56	Realization of low dislocation density AlN on a small-coalescence-area nano-patterned sapphire substrate. CrystEngComm, 2019, 21, 2490-2494.	1.3	31
57	Hole mobility in wurtzite InN. Applied Physics Letters, 2011, 98, .	1.5	30
58	High performance of AlGaN deep-ultraviolet light emitting diodes due to improved vertical carrier transport by delta-accelerating quantum barriers. Applied Physics Letters, 2019, 114, .	1.5	30
59	Demonstration of epitaxial growth of strain-relaxed GaN films on graphene/SiC substrates for long wavelength light-emitting diodes. Light: Science and Applications, 2021, 10, 117.	7.7	30
60	Influence of annealing on ZnO thin film grown by plasma-assisted MOCVD. Vacuum, 2003, 69, 473-476.	1.6	28
61	The origin and evolution of V-defects in InxAl1â^'xN epilayers grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2009, 95, .	1.5	28
62	Performance enhancement mechanisms of passivated InN/GaN-heterostructured ion-selective field-effect-transistor pH sensors. Sensors and Actuators B: Chemical, 2013, 181, 810-815.	4.0	28
63	Tuning the graphene work function by uniaxial strain. Applied Physics Letters, 2015, 106, .	1.5	28
64	Crystal quality evolution of AlN films via high-temperature annealing under ambient N₂ conditions. CrystEngComm, 2018, 20, 6613-6617.	1.3	28
65	Hexagonal BNâ€Assisted Epitaxy of Strain Released GaN Films for True Green Lightâ€Emitting Diodes. Advanced Science, 2020, 7, 2000917.	5.6	28
66	Fabrication and properties of coherent-structure In-polarity InNâ^•In0.7Ga0.3N multiquantum wells emitting at around 1.55Î¼m. Journal of Applied Physics, 2007, 102, 083539.	1.1	26
67	Search for free holes in InN:Mg-interplay between surface layer and Mg-acceptor doped interior. Journal of Applied Physics, 2009, 105, 123713.	1.1	26
68	Photoluminescence and pressure effects in short period InN/nGaN superlattices. Journal of Applied Physics, 2013, 113, 123101.	1.1	26
69	Large-Scale Synthesis and Systematic Photoluminescence Properties of Monolayer MoS2 on Fused Silica. ACS Applied Materials & Interfaces, 2016, 8, 18570-18576.	4.0	26
70	Effect of electron distribution in InN films on infrared reflectance spectrum of longitudinal optical phonon-plasmon interaction region. Journal of Applied Physics, 2008, 103, 053515.	1.1	25
71	Anomalous Hall mobility kink observed in Mg-doped InN: Demonstration of p-type conduction. Applied Physics Letters, 2010, 97, .	1.5	25
72	Shear strain induced modulation to the transport properties of graphene. Applied Physics Letters, 2014, 105, .	1.5	25

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73	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. Scientific Reports, 2015, 4, 4371.	1.6	25
74	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaN system. Scientific Reports, 2016, 6, 25124.	1.6	25
75	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes by inserting single spike barriers. Superlattices and Microstructures, 2016, 100, 941-946.	1.4	25
76	Vacancy-type defects in Mg-doped InN probed by means of positron annihilation. Journal of Applied Physics, 2009, 105, .	1.1	24
77	Observation of the photoinduced anomalous Hall effect in GaN-based heterostructures. Applied Physics Letters, 2011, 98, .	1.5	24
78	Identifying a doping type of semiconductor nanowires by photoassisted kelvin probe force microscopy as exemplified for GaN nanowires. Optical Materials Express, 2017, 7, 904.	1.6	24
79	Î²-Ga₂O₃ thin film grown on sapphire substrate by plasma-assisted molecular beam epitaxy. Journal of Semiconductors, 2019, 40, 012802.	2.0	24
80	Infrared analysis of hole properties of Mg-doped p-type InN films. Applied Physics Letters, 2008, 93, 231903.	1.5	23
81	Effect of Mg doping on enhancement of terahertz emission from InN with different lattice polarities. Applied Physics Letters, 2010, 96, .	1.5	23
82	Evidence of Type-II Band Alignment in III-nitride Semiconductors: Experimental and theoretical investigation for In0.17Al0.83N/GaN heterostructures. Scientific Reports, 2014, 4, 6521.	1.6	23
83	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. Applied Physics Letters, 2020, 116, .	1.5	23
84	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
85	Origin of Improved Optical Quality of Monolayer Molybdenum Disulfide Grown on Hexagonal Boron Nitride Substrate. Small, 2016, 12, 198-203.	5.2	22
86	High-electron-mobility InN epilayers grown on silicon substrate. Applied Physics Letters, 2018, 112, .	1.5	22
87	Sub-nanometer ultrathin epitaxy of AlGaN and its application in efficient doping. Light: Science and Applications, 2022, 11, 71.	7.7	22
88	Strain effects on InxAl1â^'xN crystalline quality grown on GaN templates by metalorganic chemical vapor deposition. Journal of Applied Physics, 2010, 107, .	1.1	21
89	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. Advanced Functional Materials, 2019, 29, 1902608.	7.8	21
90	Growth of In-polar and N-polar InN nanocolumns on GaN templates by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1561-1565.	0.8	20

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91	Broadening factors of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi>E</mml:mi><mml:mn>1</mml:mn></mml:msub><mml:mrow><mml:mo>(</mml:mo> coupled modes of hexagonal InN investigated by infrared reflectance measurements. Physical Review B, 2007, 76, .	1.1	20
92	Vacancy-type defects in InxGa1â€“xN alloys probed using a monoenergetic positron beam. Journal of Applied Physics, 2012, 112, .	1.1	20
93	Free and bound excitonic effects in Al0.5Ga0.5N/Al0.35Ga0.65N MQWs with different Si-doping levels in the well layers. Scientific Reports, 2015, 5, 13046.	1.6	20
94	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes via asymmetric step-like AlGaN quantum wells. Superlattices and Microstructures, 2017, 104, 240-246.	1.4	20
95	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
96	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. Physical Review Materials, 2020, 4, .	0.9	20
97	Excitonic localization at macrostep edges in AlGaN/AlGaN multiple quantum wells. Superlattices and Microstructures, 2017, 104, 397-401.	1.4	19
98	Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration. Advanced Materials, 2022, 34, e2106814.	11.1	19
99	Drive High Power UVCâ€LED Wafer into Lowâ€Cost 4â€inch Era: Effect of Strain Modulation. Advanced Functional Materials, 0, , 2112111.	7.8	19
100	Structural and optical properties of ZnO film by plasma-assisted MOCVD. Optical and Quantum Electronics, 2002, 34, 883-891.	1.5	18
101	Strong circular photogalvanic effect in ZnO epitaxial films. Applied Physics Letters, 2010, 97, .	1.5	18
102	Electronic structure of GaInN semiconductors investigated by x-ray absorption spectroscopy. Applied Physics Letters, 2011, 98, .	1.5	18
103	Multi-bands photoconductive response in AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2014, 104, 172108.	1.5	18
104	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGaN-based quantum wells. Scientific Reports, 2017, 7, 2358.	1.6	18
105	Highâ€Mobility Twoâ€Dimensional Electron Gas at InGaN/InN Heterointerface Grown by Molecular Beam Epitaxy. Advanced Science, 2018, 5, 1800844.	5.6	18
106	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
107	Anomalous linear photogalvanic effect observed in a GaN-based two-dimensional electron gas. Physical Review B, 2011, 84, .	1.1	17
108	Temperature sensitive photoconductivity observed in InN layers. Applied Physics Letters, 2013, 102, .	1.5	17

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109	Effect of injection current on the optical polarization of AlGaN-based ultraviolet light-emitting diodes. Optics Express, 2014, 22, 19589.	1.7	17
110	Electronic properties of polycrystalline graphene under large local strain. Applied Physics Letters, 2014, 104, .	1.5	17
111	Positive temperature coefficient of photovoltaic efficiency in solar cells based on InGaN/GaN MQWs. Applied Physics Letters, 2016, 109, .	1.5	17
112	Latticeâ€Symmetryâ€Driven Epitaxy of Hierarchical GaN Nanotripods. Advanced Functional Materials, 2017, 27, 1604854.	7.8	17
113	Repeatable asymmetric resonant tunneling in AlGaN/GaN double barrier structures grown on sapphire. Applied Physics Letters, 2019, 114, .	1.5	17
114	Greatly enhanced performance of AlGaN-based deep ultraviolet light emitting diodes by introducing a polarization modulated electron blocking layer. Optics Express, 2019, 27, A1458.	1.7	17
115	Effect of Precise Control of V/III Ratio on In-Rich InGaN Epitaxial Growth. Japanese Journal of Applied Physics, 2006, 45, L1259-L1262.	0.8	16
116	Terahertz electroluminescence of surface plasmons from nanostructured InN layers. Applied Physics Letters, 2010, 96, .	1.5	16
117	Detection of spin-orbit coupling of surface electron layer via reciprocal spin Hall effect in InN films. Applied Physics Letters, 2012, 101, .	1.5	16
118	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16
119	Controlled bunching approach for achieving high efficiency active region in AlGaN-based deep ultraviolet light-emitting devices with dual-band emission. Applied Physics Letters, 2020, 116, .	1.5	16
120	Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. Applied Physics Letters, 2020, 116, .	1.5	16
121	In situ spectroscopic ellipsometry in plasma-assisted molecular beam epitaxy of InN under different surface stoichiometries. Journal of Applied Physics, 2006, 99, 044913.	1.1	15
122	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. Applied Physics Letters, 2018, 112, .	1.5	15
123	Improved light extraction efficiency of AlGaN deep-ultraviolet light emitting diodes combining Ag-nanodots/Al reflective electrode with highly transparent p-type layer. Optics Express, 2021, 29, 2394.	1.7	15
124	Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	1.6	14
125	Colorâ€Tunable 3D InGaN/GaN Multiâ€Quantumâ€Well Lightâ€Emittingâ€Diode Based on Microfacet Emission and Programmable Driving Power Supply. Advanced Optical Materials, 2021, 9, .	3.6	14
126	Realization of high efficiency AlGaN-based multiple quantum wells grown on nano-patterned sapphire substrates. CrystEngComm, 2021, 23, 1201-1206.	1.3	14

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127	Anisotropic damping of longitudinal optical phonon-plasmon coupling modes of InN films. Applied Physics Letters, 2008, 92, .	1.5	13
128	Lattice polarity detection of InN by circular photogalvanic effect. Applied Physics Letters, 2009, 95, .	1.5	13
129	Magnetotransport properties of lattice-matched In0.18Al0.82N/AlN/GaN heterostructures. Journal of Applied Physics, 2011, 109, 016102.	1.1	13
130	Effect of polarization on intersubband transition in AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2013, 102, .	1.5	13
131	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. Applied Physics Express, 2013, 6, 021001.	1.1	13
132	Intersubband Transition in GaN/InGaN Multiple Quantum Wells. Scientific Reports, 2015, 5, 11485.	1.6	13
133	High-quality AlN epitaxy on sapphire substrates with sputtered buffer layers. Superlattices and Microstructures, 2017, 105, 34-38.	1.4	13
134	Stress evolution in AlN growth on nano-patterned sapphire substrates. Applied Physics Express, 2020, 13, 015504.	1.1	13
135	Influence of high-energy local orbitals and electron-phonon interactions on the band gaps and optical absorption spectra of hexagonal boron nitride. Physical Review B, 2020, 102, .	1.1	13
136	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. Applied Physics Letters, 2020, 117, .	1.5	13
137	A GaN/AlN quantum cascade detector with a broad response from the mid-infrared (4.1â€‰Î¼m) to the visible (550â€‰nm) spectral range. Applied Physics Letters, 2020, 116, 171102.	1.5	13
138	Two-step growth of ZnO thin films on diamond/Si by low-pressure metal-organic chemical vapour deposition. Journal Physics D: Applied Physics, 2002, 35, L74-L76.	1.3	12
139	Cathodoluminescence Study on Spatial Luminescence Properties of InN/GaN Multiple Quantum Wells Consisting of 1-Monolayer-Thick InN Wells/GaN Matrix. Journal of Electronic Materials, 2008, 37, 597-602.	1.0	12
140	Intersubband transitions at atmospheric window in AlxGa1â^'xN/GaN multiple quantum wells grown on GaN/sapphire templates adopting AlN/GaN superlattices interlayer. Applied Physics Letters, 2011, 98, 132105.	1.5	12
141	Deep donor state in InN: Temperature-dependent electron transport in the electron accumulation layers and its influence on Hall-effect measurements. Applied Physics Letters, 2011, 99, 182107.	1.5	12
142	Dependence of Mg acceptor levels in InN on doping density and temperature. Journal of Applied Physics, 2011, 110, .	1.1	12
143	Elastic properties of indium nitrides grown on sapphire substrates determined by nano-indentation: In comparison with other nitrides. AIP Advances, 2015, 5, .	0.6	12
144	Period size effect induced crystalline quality improvement of AlN on a nano-patterned sapphire substrate. Japanese Journal of Applied Physics, 2019, 58, 100912.	0.8	12

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145	Direct evidence of hydrogen interaction with carbon: Câ€“H complex in semi-insulating GaN. Applied Physics Letters, 2020, 116, .	1.5	12
146	Controlling Phaseâ€Coherent Electron Transport in IIIâ€Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaN/GaN Double Barrier Structures. Advanced Functional Materials, 2021, 31, 2007216.	7.8	12
147	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGaN buffer layer. Applied Physics Letters, 2021, 118, .	1.5	12
148	Characteristics of InAs quantum dots on GaAs/InP with different InAs coverage. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2523.	1.6	11
149	Abnormal magnetic-field dependence of Hall coefficient in InN epilayers. Applied Physics Letters, 2009, 95, .	1.5	11
150	Identification of the main contributions to the conductivity of epitaxial InN. Physical Review B, 2011, 84, .	1.1	11
151	Determination of the surface band bending in In_xGa_{1â^'x}N films by hard x-ray photoemission spectroscopy. Science and Technology of Advanced Materials, 2013, 14, 015007.	2.8	11
152	Strain effect on the optical polarization properties of c-plane Al_026Ga_074N/GaN superlattices. Optics Express, 2014, 22, 6322.	1.7	11
153	Enhanced transport properties in InAlGaN/AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. Applied Physics Letters, 2017, 110, .	1.5	11
154	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
155	Dominant Influence of Interface Roughness Scattering on the Performance of GaN Terahertz Quantum Cascade Lasers. Nanoscale Research Letters, 2019, 14, 206.	3.1	11
156	Three Subband Occupation of the Twoâ€Dimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. Advanced Functional Materials, 2020, 30, 2004450.	7.8	11
157	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. Advanced Functional Materials, 2021, 31, 2009771.	7.8	11
158	Control of dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies introduced through thermal desorption of heteroatoms. Applied Physics Letters, 2021, 118, .	1.5	11
159	Growth of High Mobility InN Film on Gaâ€Polar GaN Substrate by Molecular Beam Epitaxy for Optoelectronic Device Applications. Advanced Materials Interfaces, 2023, 10, .	1.9	11
160	Four-inch high quality crack-free AlN layer grown on a high-temperature annealed AlN template by MOCVD. Journal of Semiconductors, 2021, 42, 122804.	2.0	11
161	In situ spectroscopic ellipsometry and RHEED monitored growth of InN nanocolumns by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 496-499.	0.7	10
162	Effect of GaN interlayer on polarity control of epitaxial ZnO thin films grown by molecular beam epitaxy. Applied Physics Letters, 2010, 97, 151908.	1.5	10

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163	Ionic liquid gated electric-double-layer transistors based on Mg-doped InN epitaxial films. Applied Physics Letters, 2013, 103, .	1.5	10
164	Formation of p-n-p junction with ionic liquid gate in graphene. Applied Physics Letters, 2014, 104, .	1.5	10
165	Mid-infrared Photoconductive Response in AlGaN/GaN Step Quantum Wells. Scientific Reports, 2015, 5, 14386.	1.6	10
166	Study on AlGaN P-I-N-I-N solar-blind avalanche photodiodes with Al0.45Ga0.55N multiplication layer. Electronic Materials Letters, 2015, 11, 1053-1058.	1.0	10
167	Effect of indium droplets on growth of InGaN film by molecular beam epitaxy. Superlattices and Microstructures, 2018, 113, 650-656.	1.4	10
168	Improved Ohmic contacts to plasma etched high Al fraction n-AlGaN by active surface pretreatment. Applied Physics Letters, 2021, 118, .	1.5	10
169	Monolayer-Scale GaN/AlN Multiple Quantum Wells for High Power e-Beam Pumped UV-Emitters in the 240â€“270 nm Spectral Range. Nanomaterials, 2021, 11, 2553.	1.9	10
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